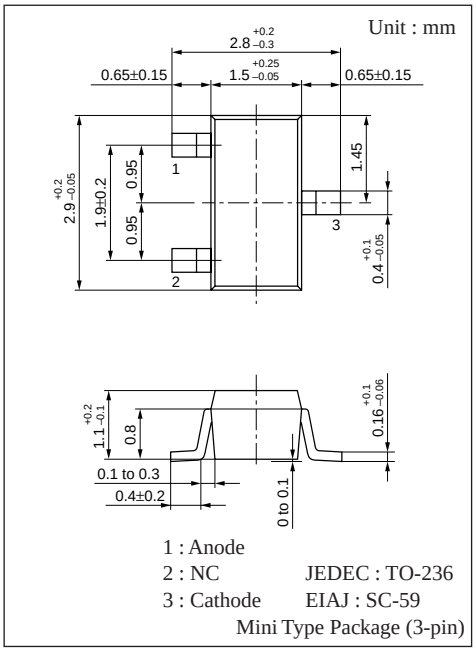
MA788

Silicon epitaxial planer type

For super high-speed switching circuit
For small current rectification

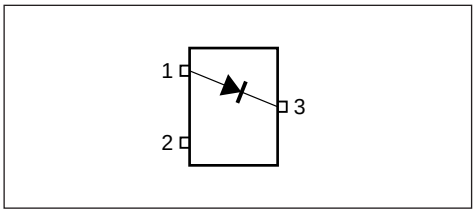
■ Features

- $I_{F(AV)}$=200mA rectification possible
- Reverse voltage V_R (DC value)= 60V guaranteed



Marking Symbol : M3V

■ Internal Connection



■ Absolute Maximum Ratings (Ta= 25˚C)

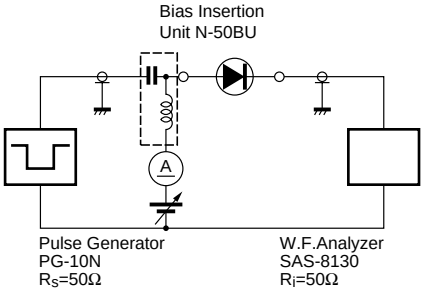
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	60	V
Repetitive peak reverse voltage	V_{RRM}	60	V
Peak forward current	I_{FM}	300	mA
Average forward current	$I_{F(AV)}$	200	mA
Non-repetitive peak forward surge current	I_{FSM}*	1	A
Junction temperature	T_j	125	˚C
Storage temperature	T_{stg}	– 55 to +125	˚C

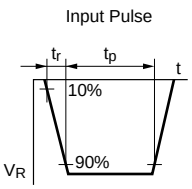
* 50Hz sine wave, one-cycle wave, high value (non-repetitive)

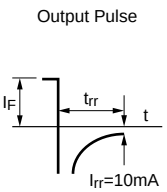
■ Electrical Characteristics (Ta= 25˚C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R= 50V			50	µA
Forward voltage (DC)	V_F	I_F= 200mA			0.65	V
Terminal capacitance	C_t	V_R = 0V, f=1MHz		30		pF
Reverse recovery time	t_{rr}*	I_F = I_R=100mA I_{rr}= 10mA , R_L=100Ω		3		ns

Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.
2. Rated input/output frequency : 1000MHz
3. * t_{rr} measuring circuit

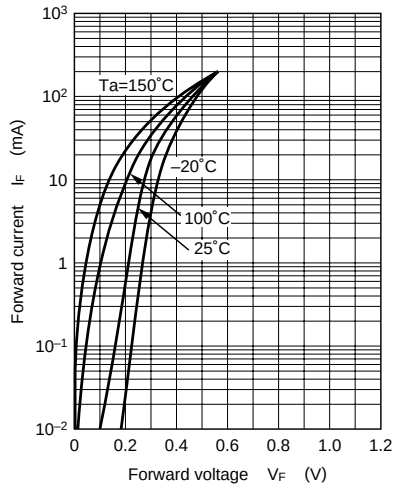




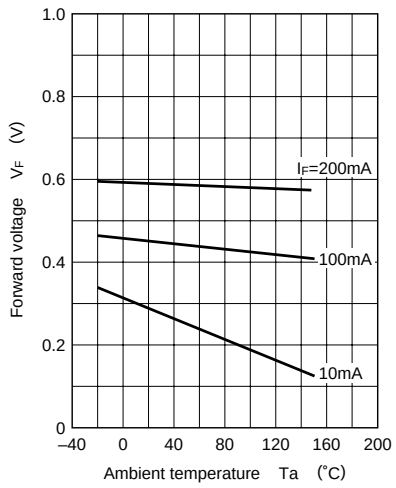


■ Marking

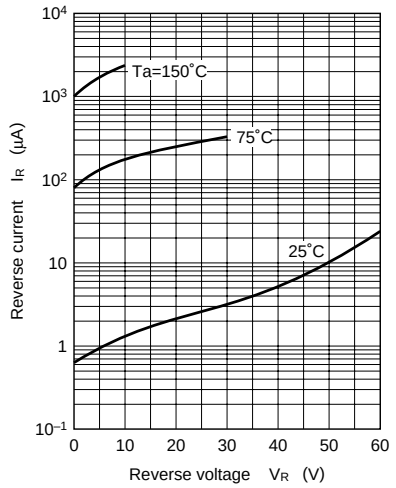
$I_F - V_F$



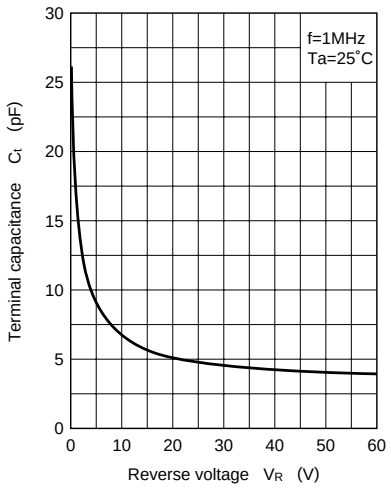
$V_F - Ta$



$I_R - V_R$



$C_t - V_R$



$I_R - Ta$